Section 0

SYSTEM DESCRIPTION:

SPECIFICATIONS

MODEL:	Cee (Cost effective equipment) Model 1000 Hotplate.
TEMPERATURE CONTROL:	PID (Proportional Integral Derivative) Microprocessor controlled to a maximum temperature of 300° C (400° C optional) with 1.0°-C resolution (0.1° C optional).
SUBSTRATE SIZE:	Standard capacities of 0.5 to 6 inches depending on model and/or retrofit. Custom chuck configurations also available.
EXHAUST COVER:	Cee open-faced single lip exhaust cover supplied as standard equipment in all hotplates.
POWER SUPPLY:	120 Volts AC (240 Volt AC, optional), 700 Watts.
UTILITIES:	Nitrogen gas: 35 psi minimum; Vacuum: 25" Hg.
DIMENSIONS:	11" height x 18" length x 13.2" depth.
WEIGHT:	46 lb

Section 0

SYSTEM DESCRIPTION:

FEATURES

- The Model 1000 Hotplate supports three bake methods: proximity, soft-contact, and hard-contact (For more information see bake methods, Section 3). These bake methods provide maximum control of substrate warmup, solvent drying, and resin curing characteristics.

- A removable, portable timer measures bake time. The operator can carry the timer during long, bake cycles; this conveniently keeps the operator in touch with the unit.

- A microprocessor-driven, three-mode controller permits precise control of temperature critical processes. The Model 1000 Hotplate realizes a bake temperature resolution of 1.0° C and maximum temperature of 300° C (0.1° C and/or 400° C optional, respectively).

- Easily installed retrofits facilitate changing substrate size from large photomasks to silicon or GaAs wafers less than 1 inch in diameter.

- A benchtop unit, the Model 1000 Hotplate covers less than two-square feet and requires only common utilities: 120 Volts AC, nitrogen gas, and vacuum.